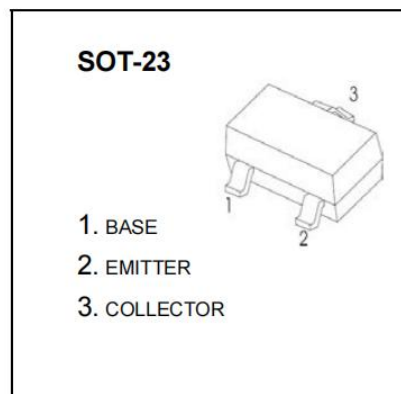


NPN Silicon AF and Switching Transistor

- For general AF applications
- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary type: BCX42 (PNP)



Type	Marking	Pin Configuration			Package
BCX41	EKs	1 = B	2 = E	3 = C	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	125	V
Collector-base voltage	V_{CBO}	125	
Emitter-base voltage	V_{EBO}	5	
Collector current	I_C	800	mA
Peak collector current, $t_p \leq 10$ ms	I_{CM}	1	A
Base current	I_B	100	mA
Peak base current	I_{BM}	200	
Total power dissipation $T_S \leq 79^\circ\text{C}$	P_{tot}	330	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 215	K/W

¹⁾For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 10\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	125	-	-	V
Collector-base breakdown voltage $I_C = 100\text{ }\mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	125	-	-	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	5	-	-	
Collector-base cutoff current $V_{CB} = 100\text{ V}, I_E = 0$ $V_{CB} = 100\text{ V}, I_E = 0, T_A = 150^\circ\text{C}$	I_{CBO}	- -	- -	0.1 20	μA
Collector-emitter cutoff current $V_{CE} = 100\text{ V}, T_A = 85^\circ\text{C}$ $V_{CE} = 100\text{ V}, T_A = 125^\circ\text{C}$	I_{CEO}	- -	- -	10 75	
Emitter-base cutoff current $V_{EB} = 4\text{ V}, I_C = 0$	I_{EBO}	-	-	100	nA
DC current gain ¹⁾ $I_C = 100\text{ }\mu\text{A}, V_{CE} = 1\text{ V}$ $I_C = 100\text{ mA}, V_{CE} = 1\text{ V}$ $I_C = 200\text{ mA}, V_{CE} = 1\text{ V}$	h_{FE}	25 63 40	- - -	- - -	-
Collector-emitter saturation voltage ¹⁾ $I_C = 300\text{ mA}, I_B = 30\text{ mA}$	V_{CEsat}	-	-	0.9	V
Base emitter saturation voltage ¹⁾ $I_C = 300\text{ mA}, I_B = 30\text{ mA}$	V_{BEsat}	-	-	1.4	

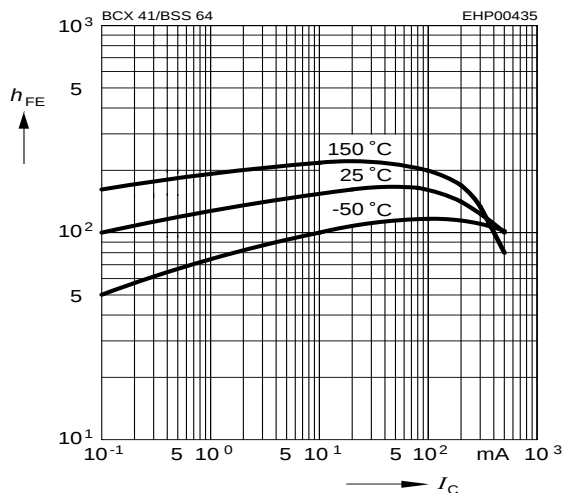
AC Characteristics

Transition frequency $I_C = 20\text{ mA}, V_{CE} = 5\text{ V}, f = 20\text{ MHz}$	f_T	-	100	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}, f = 1\text{ MHz}$	C_{cb}	-	12	-	pF

¹⁾Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

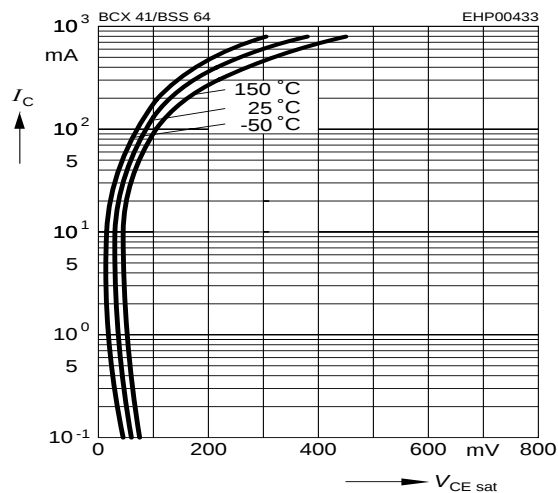
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 1\text{ V}$



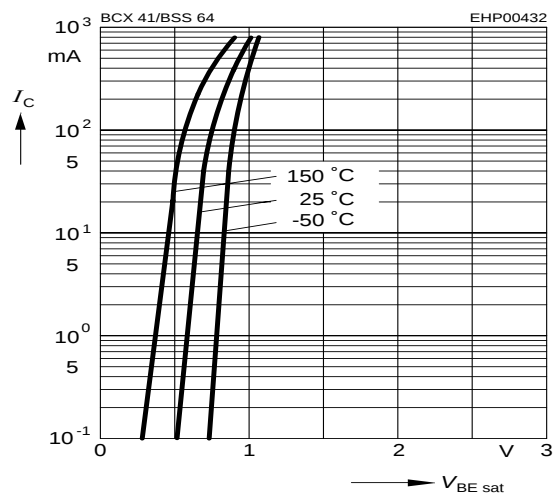
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 10$



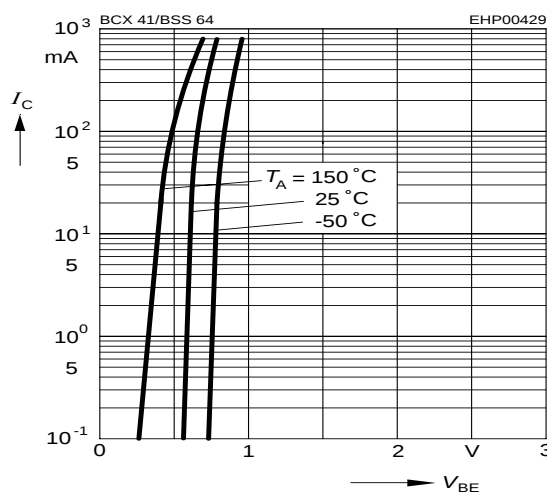
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 10$



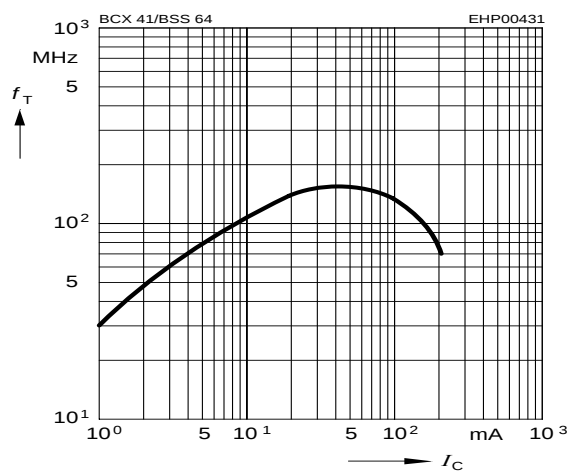
Collector current $I_C = f(V_{BE})$

$V_{CE} = 1\text{ V}$



Transition frequency $f_T = f(I_C)$

$V_{CE} = \text{parameter in V}, f = 2\text{ GHz}$



Total power dissipation $P_{tot} = f(T_S)$

